News Release

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Freescale to showcase expanded RF portfolio for commercial aerospace applicatio

Industry's first 1kW LDMOS field effect transistor operating at L-band frequency to be fea
Boston

AUSTIN, Texas – June 2, 2009 – Freescale Semiconductor has introduced five laterally d
semiconductor (LDMOS) field effect transistors (FETs) for commercial aerospace applica
RF portfolio includes L-band (965 MHz to 1215 MHz) devices and the first LDMOS FETs
applications at S-band (3.1 GHz to 3.5 GHz). Freescale will showcase these devices at B
International Microwave Symposium (IMS 2009) in Boston, June 7-12.

The RF power transistors are designed to deliver the highest RF output power, efficiency
class. The exceptionally rugged devices are ideal for pulsed-signal applications, such as
distance measuring equipment (DME) and weather radar.

Freescale's expanded RF portfolio for aerospace applications includes:

MRF6VP121KH/HS – 965 MHz to 1215 MHz, 1kW peak, (100 W average output), 128 µs
duty cycle, 50 Vdc, 20 dB gain, 56% efficiency at 1030 MHz.

MRF6V12500H/HS – 965 MHz to 1215 MHz, 500 W peak, (50 W average output), 128 µs
duty cycle, 50 Vdc, 19 dB gain, 60% efficiency at 1030 MHz. Designed to handle full rate
10:1 VSWR.

MRF6V12250H/HS – 965 MHz to 1215 MHz, 275 W peak, (27.5 W average output), 128
10% duty cycle, 50 Vdc, 20.3 dB gain, 65.5% efficiency at 1030 MHz. Designed to handle
power into 10:1 VSWR.

MRF7S35120HS – 3.1 GHz to 3.5 GHz, 120 W peak, (24 W average output), 100 µsec p
cycle, 32 Vdc, 12 dB gain and 40% efficiency at 3.5 GHz. Designed to handle full rated p
VSWR.

MRF7S35015H – 3.1 GHz to 3.5 GHz, 15 W peak, (3 W average output), 100 µsec pulse
cycle, 32 Vdc, 16 dB gain and 41% efficiency at 3.5 GHz. Designed to handle full rated p
VSWR.

Like other Freescale commercial aerospace RF power transistors, the latest devices are
incorporate electrostatic discharge (ESD) protection. This ESD circuitry enables a broad
-6 V to +10 V to help improve performance when the devices are operating in higher effic
as Class C.

Pricing and availability
The MRF6VP121KH/HS, MRF6V12250H/HS, MRF7S35120HS and the MRF7S35015H
production. The MRF6V12500H/HS is expected to be in production in September 2009.
sampling, and reference test fixtures are available now. Large-signal models for L-band d
in September 2009. For sampling and pricing information, please contact a Freescale sal
an authorized distributor.

Visit Freescale's booth #2018 at IMS MTT-S. For up-to-the-minute show updates, follow
Twitter: www.twitter.com/RFLeonard.

For more information about Freescale's RF power transistor portfolio, visit www.freescale.c
www.freescale.com/rfaerospace.

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the automotive, consumer, industrial and networking markets. The privately held company i
Texas, and has design, research and development, manufacturing or sales operations arou
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